



STB4NK60Z-1 Information



For Reference Only

Part Number STB4NK60Z-1
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 4A I2PAK

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









STB4NK60Z-1 Specifications

Manufacturer Part Number Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series SuperMESH? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 4A (Te) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 26nC @ 10V Input Capacitance (Ciss) (Max) @ Vds \$30V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 150°C (TJ) Mounting Type Through Hole Supplier Device Package 12PAK Package / Case TO-262-3 Long Leads, 12Pak, TO-262AA		
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Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 50μAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds510pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)70W (Tc)Rds On (Max) @ Id, Vgs2 Ohm @ 2A, 10VOperating Temperature150°C (TJ)Mounting TypeThrough HoleSupplier Device Package12PAKPackage / CaseTO-262-3 Long Leads, 12Pak, TO-262AA	Drain to Source Voltage (Vdss)	600V
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Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Mounting Type Through Hole Supplier Device Package Package / Case 26nC @ 10V 510pF @ 25V 510pF @ 25V - 70W (Tc) 70W (Tc)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 510pF @ 25V Vgs (Max) ET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2 Ohm @ 2A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs(th) (Max) @ Id	4.5V @ 50μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 70W (Tc) Rds On (Max) @ Id, Vgs 2 Ohm @ 2A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Gate Charge (Qg) (Max) @ Vgs	26nC @ 10V
FET Feature - To-262-3 Long Leads, I2Pak, TO-262AA	Input Capacitance (Ciss) (Max) @ Vds	510pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 2 Ohm @ 2A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Vgs (Max)	±30V
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Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Power Dissipation (Max)	70W (Tc)
Mounting Type Through Hole Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Rds On (Max) @ Id, Vgs	2 Ohm @ 2A, 10V
Supplier Device Package I2PAK Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Operating Temperature	150°C (TJ)
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Mounting Type	Through Hole
	Supplier Device Package	I2PAK
Report errors?	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
I .		Report errors?

STB4NK60Z-1 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STB4NK60Z-1 Payment Methods



















STB4NK60Z-1 Shipping Methods













If you have any question about STB4NK60Z-1, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com